

**Amendments to the Claims:**

This listing of claims replaces all prior versions, and listings, of claims of this application:

**Listing of Claims:**

1-6. (Canceled).

7. (Currently amended) ~~The MRAM according to Claim 6~~ A Magnetic Random Access Memory (MRAM) device comprising:

an array of magnetic memory cells arranged in intersecting rows and columns;

a plurality of magnetic memory cell selection devices, each of which is coupled to a respective one of the magnetic memory cells in the array to enable selective access to any of the magnetic memory cells during a write operation, wherein ~~the~~ a number of the rows and columns included in the device array is limited according to the relation:

$$\eta = \sqrt{\frac{R_m * \varepsilon (2 + K_{DR})}{R_r (1 - \varepsilon)}}$$

where  $R_m$  comprises a resistance of one of the magnetic memory cells,  $\varepsilon$  comprises a maximum current non-uniformity of the array during a write operation,  $K_{DR}$  depends on ~~the~~ a reverse bias resistance of one of the magnetic memory cell selection devices, and  $R_r$  comprises a resistance of a row or column of the magnetic memory cells.

8. (Previously presented) The MRAM according to Claim 7 wherein the maximum current non-uniformity of the array comprises less than about 15 percent.

9. (Canceled).

10. (Currently amended) The MRAM according to Claim [[6]] 7 wherein the magnetic memory cell selection devices comprises diodes or transistors.

11. (Canceled).

12. (Currently amended) ~~The method according to Claim 11~~ A method of sizing a MRAM comprising:

determining a maximum current non-uniformity for the MRAM array to be provided by the array during a write operation wherein the maximum number of rows and columns for inclusion in the device is limited according to the relation:

$$\eta = \sqrt{\frac{R_m * \varepsilon (2 + K_{DR})}{R_r (1 - \varepsilon)}}$$

where  $R_m$  comprises a cell resistance of one of the magnetic memory cells,  $\varepsilon$  comprises a maximum current non-uniformity of the array during a write operation,  $K_{DR}$  depends on the reverse bias resistance of one of the magnetic memory cell selection devices, and  $R_r$  comprises a resistance of a row or column of the magnetic memory cells

13. (Previously presented) The method according to Claim 12 wherein the maximum current non-uniformity of the array comprises less than about 15 percent.

14. (Canceled).

15. (Currently amended) The method according to Claim [[11]] 12 wherein the magnetic memory cell selection devices comprises diodes or transistors.

16. (Canceled).